









# CEF38N65SA

650V ▲ 80mΩ ▲ 39ANote 4 ▲ Si MOSFET

SILICON Si MOSFET ▲ THT type
N-channel enhancement mode
UL94V-0 rated flame retardant epoxy

TO220F-3L package ▲ Electrical insulated mounting tab

Super high dense cell density for extremely low R<sub>DS(ON)</sub>

High power and current handling capability

#### **MAXIMUM RATINGS**

Parameter ( $T_c$ = 25°C, unless otherwise noted)		Characteristics
Drain-Source Voltage	V <sub>DS</sub>	650V
Gate-Source Voltage	V <sub>GS</sub>	±30V
Continuous Drain Current at T <sub>C</sub> = 25°C	I <sub>D</sub>	39A Note 4
Continuous Drain Current at T <sub>C</sub> = 100°C	I <sub>D</sub>	24.5A Note 4
Pulsed Drain Current Note 1	I <sub>DM</sub> Note 5	155.2A Note 4
Maximum Power Dissipation at T <sub>C</sub> = 25°C	P <sub>D</sub>	89W
Power Dissipation Derating above 25°C	ΔP <sub>D</sub>	0.7W/°C
Single Pulsed Avalanche Energy Note 6	E <sub>AS</sub>	735mJ
Single Pulsed Avalanche Current Note 6	l <sub>AS</sub>	7A
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +150°C

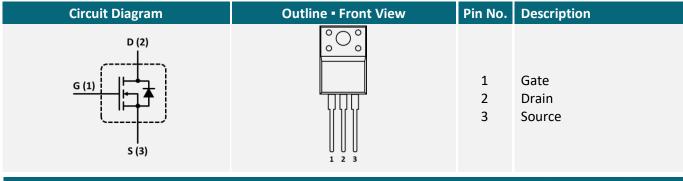
#### THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R <sub>TH_JC</sub>	1.4°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>TH JA</sub>	65°C/W

# **APPLICATIONS**

EV Charging	Industrial Inverters	Motors & Drives	Power Factor Correction	Renewable Energy	SMPS	UPS
<b>₹</b>			PFC	*		

# **PIN DESCRIPTION**





# **ELECTRICAL CHARACTERISTICS** ▲ T<sub>C</sub> = 25°C, unless otherwise noted

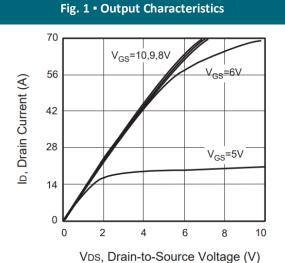
ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$ , $I_D = 250\mu A$	$BV_DSS$	650			V
Zero Gate Voltage Drain Current	$V_{DS} = 650V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 30V, V_{DS} = 0V$	I <sub>GSSF</sub>			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -30V$ , $V_{DS} = 0V$	I <sub>GSSR</sub>			-100	nA
On Characteristics Note 2						
Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250 \mu A$	$V_{GS(th)}$	2.5		4.5	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 20A$	R <sub>DS(ON)</sub>		80	95	mΩ
Dynamic Characteristics Note 3						
Input Capacitance	$V_{DS} = 150V$ , $V_{GS} = 0V$ , $f = 1MHz$	C <sub>ISS</sub>		1915		pF
Output Capacitance	$V_{DS} = 150V$ , $V_{GS} = 0V$ , $f = 1MHz$	Coss		110		pF
Reverse Transfer Capacitance	$V_{DS} = 150V$ , $V_{GS} = 0V$ , $f = 1MHz$	C <sub>RSS</sub>		5		pF
Switching Characteristics Note 3						
Turn-On Delay Time	$V_{DD}$ = 520V, $V_{GS}$ = 10V, $I_D$ = 20A, $R_{G(ext)}$ = $6\Omega$	t <sub>D(ON)</sub>		37		ns
Turn-On Rise Time	$V_{DD}$ = 520V, $V_{GS}$ = 10V, $I_D$ = 20A, $R_{G(ext)}$ = $6\Omega$	t <sub>R</sub>		17		ns
Turn-Off Delay Time	$V_{DD}$ = 520V, $V_{GS}$ = 10V, $I_D$ = 20A, $R_{G(ext)}$ = $6\Omega$	t <sub>D(OFF)</sub>		95		ns
Turn-Off Fall Time	$V_{DD}$ = 520V, $V_{GS}$ = 10V, $I_D$ = 20A, $R_{G(ext)}$ = $6\Omega$	t <sub>F</sub>		9		ns
Total Gate Charge	$V_{DS} = 520V$ , $V_{GS} = 10V$ , $I_D = 20A$	$Q_{G}$		69		nC
Gate Source Charge	$V_{DS} = 520V$ , $V_{GS} = 10V$ , $I_D = 20A$	$Q_{GS}$		12		nC
Gate Drain Charge	$V_{DS} = 520V$ , $V_{GS} = 10V$ , $I_D = 20A$	$Q_{GD}$		30		nC
<b>Drain-Source Diode Characteristics a</b>	nd Maximum Ratings					
Drain-Source Diode					19	Α
Forward Current		I <sub>S</sub>			19	A
Drain-Source Diode Forward Voltage Note 2	$V_{GS} = 0V$ , $I_S = 19A$	$V_{SD}$			1.5	V
Reverse Recovery Time	$V_R = 25V$ , $I_F = 10A$ , $dI_F/dt = 100A/\mu s$	$t_{RR}$		324		ns
Reverse Recovery Charge	$V_R = 25V$ , $I_F = 10A$ , $dI_F/dt = 100A/\mu s$	$Q_{RR}$		4.2		μC
Maximum Diode Commutation Speed	$V_{DS} = 0400V$ , $I_{SD} \le 20A$ , $T_J = 25$ °C	di <sub>F</sub> /dt			1300	A/μs

#### Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 3: Guaranteed by design, not subject to production testing.
- 4: Limited only by maximum temperature allowed.
- 5: Pulse width limited by safe operating area.
- 6: L = 30mH,  $I_{AS}$  = 7A,  $V_{DD}$  = 60V,  $R_{G}$  = 25Ω, Starting  $T_{J}$  = 25°C



#### REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



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Fig. 2 • Transfer Characteristics

3000 2500 C, Capacitance (pF) Ciss 2000 1500 1000 500 Coss C<sub>rss</sub> 0 1 30 60 150 0 120 VDS, Drain-to-Source Voltage (V)

Fig. 3 • Capacitance

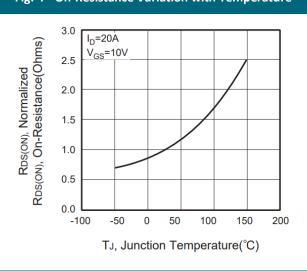
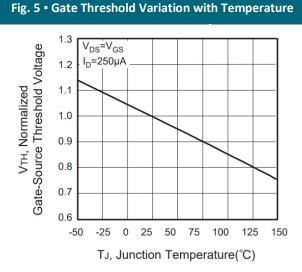
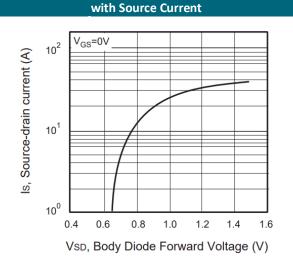


Fig. 6 • Body Diode Forward Voltage Variation





MGT ▲ Manufacturer Group of Technology



#### REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 7 • Gate Charge

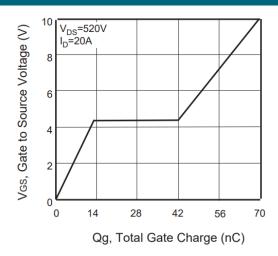


Fig. 8 • Maximum Safe Operating Area

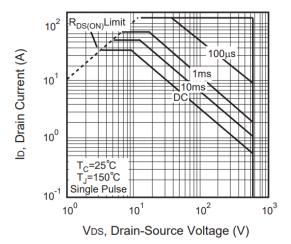
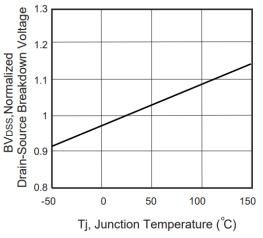


Fig. 9 • Breakdown Voltage Variation vs. Temperature





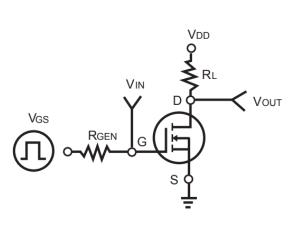
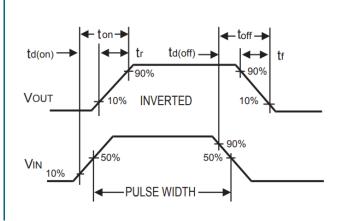


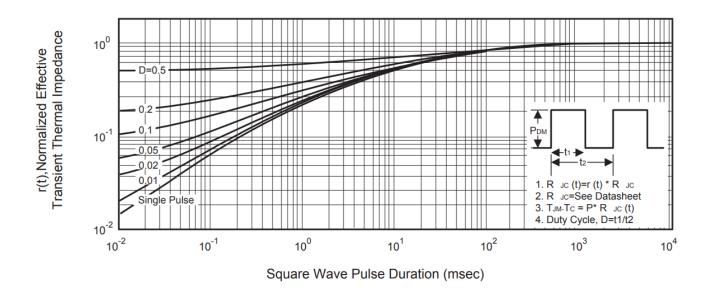
Fig. 11 • Switching Waveforms





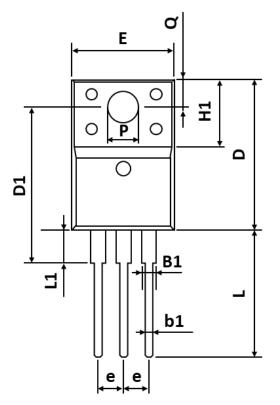
# REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

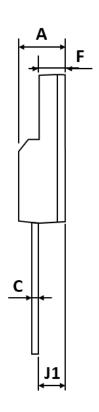
# Fig. 12 • Normalized Thermal Transient Impedance Curve





# **PACKAGE OUTLINE**





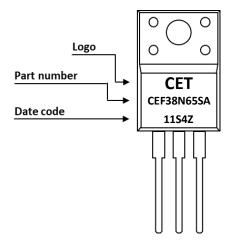
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Α	4.500	-	5.000
B1	1.000	-	1.500
b1	0.700	-	0.950
С	0.420	-	0.700
D	15.670	-	16.070
D1	14.800	-	16.000
E	9.960	-	10.360
е	2.340	-	2.740
F	2.340	-	2.740
H1	6.480	-	6.900
J1	2.550	-	2.950
L	12.080	-	13.480
L1	2.230	-	3.650
Q	3.100	-	3.500
Р	2.980	-	3.380

# **ORDERING INFORMATION**

Part Number	Package	Packing	Tube Qty.	Inner Box Qty.	Outer Box Qty.
CEF38N65SA	TO-220F-3L	Tube	50pcs	1,000pcs	4,000pcs

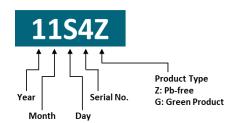


#### **PART MARKING**



#### **DATE CODE**

Example: 11S4Z



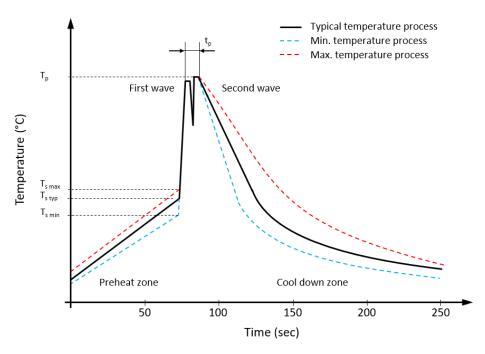


Coding list for "Day"





# RECOMMENDED WAVE SOLDERING PROFILE A THT PACKAGE



# Classification wave soldering profile ▲ Refer to EN 61760-1: 2006

Profile Features		Value ▲ Sn-Pb Assembly	Value ▲ Pb-free Assembly
Preheat temperature min.	$T_{smin}$	100 °C	100 °C
Preheat temperature typical	T <sub>s typ</sub>	120 °C	120 °C
Preheat temperature max.	$T_{smax}$	130 °C	130 °C
Preheat time $t_s$ from $T_{smin}$ to $T_{smax}$	ts	70 seconds	70 seconds
Peak temperature	$T_p$	235 °C to 260 °C	245 °C to 260 °C
Time of actual peak temperature	t <sub>p</sub>	Max. 10 seconds Max. 5 second each wave	Max. 10 seconds Max. 5 second each wave
Ramp-down date min.		~ 2 °C/second	~ 2 °C/second
Ramp-down rate typical		~ 3.5 °C/second	~ 3.5 °C/second
Ramp-down rate max.		~ 5 °C/second	~ 5 °C/second
Time 25°C to 25°C		4 minutes	4 minutes



#### **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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